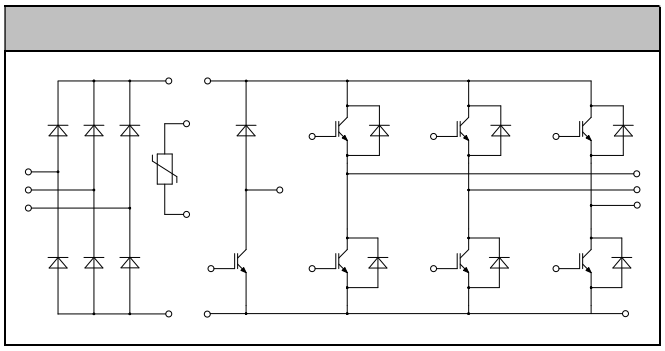
MG50P12E2

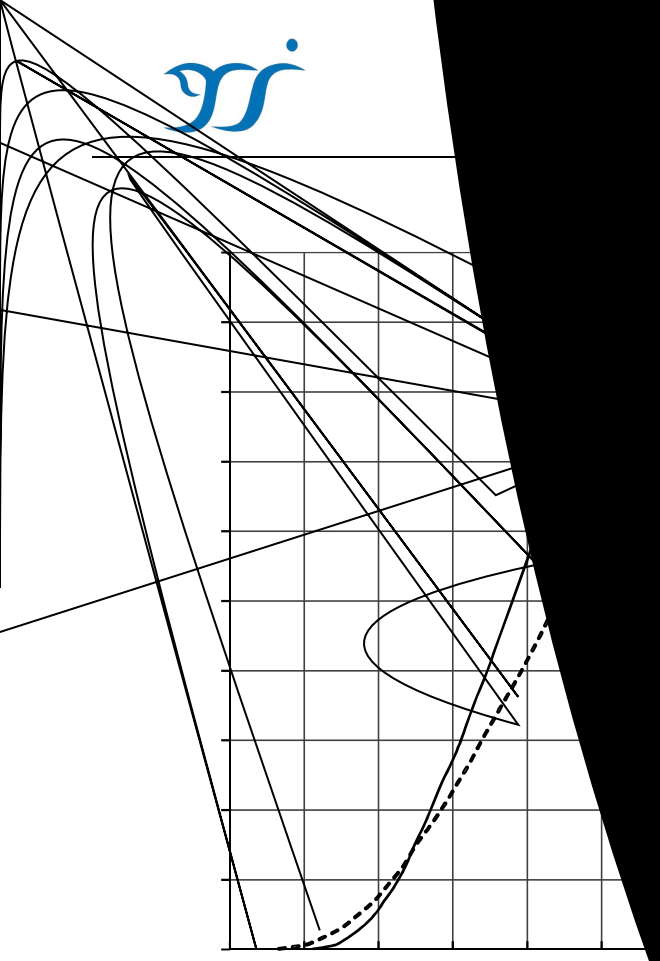


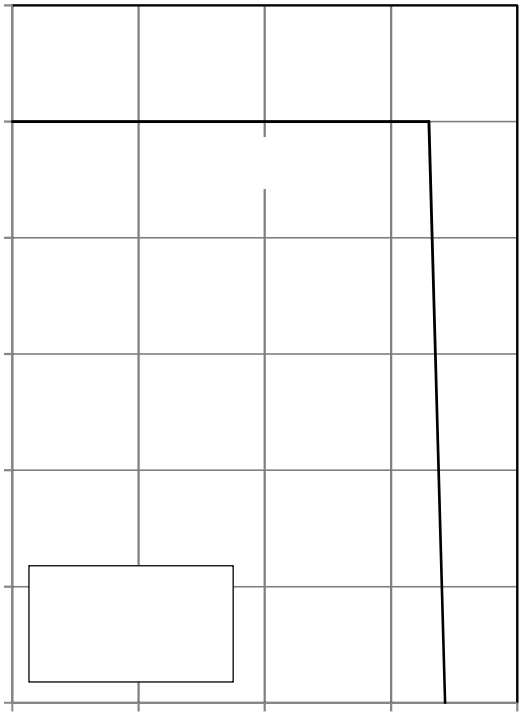
℃

		℃				
		℃				

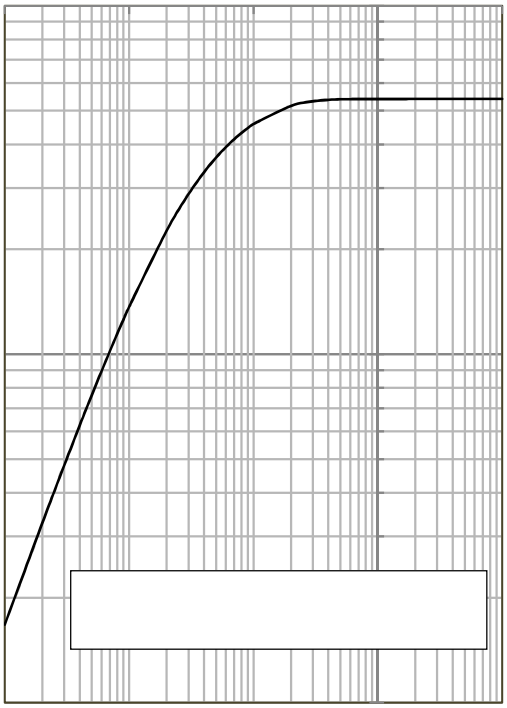
		℃				
		℃				

Isolation voltage	V	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T				175	
Operating Junction Temperature	T		-40		150	
Storage Temperature	T		-40		125	
Stray-inductance-module	L			60		
Module lead resistance, terminals-chip	R	T =25 , per switch		4.0		
	R			3.0		
Thermal Resistance Junction-to Case	R	per IGBT-inverter			0.52	K/W
		per Diode-inverter			0.81	
		per IGBT-brake-copper			0.66	
		per Diode-chopper			1.50	
		per Diode-rectifier			0.64	
Thermal Resistance Case-to Sink	R	per IGBT-inverter		0.29		K/W
		per Diode-inverter		0.44		
		per IGBT-brake-copper		0.32		
		per Diode-chopper		0.33		
		per Diode-rectifier		0.70		
		per Module		0.009		
Mounting Force Per Clamp	F		3.0		6.0	N
Weight of Module	G			300		g

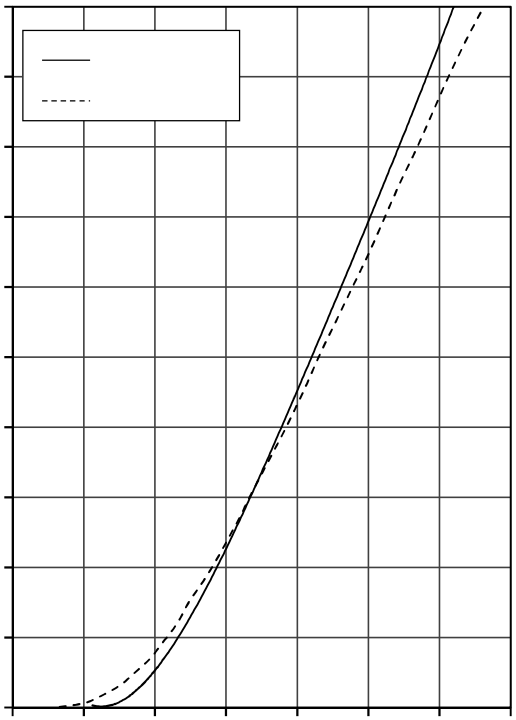




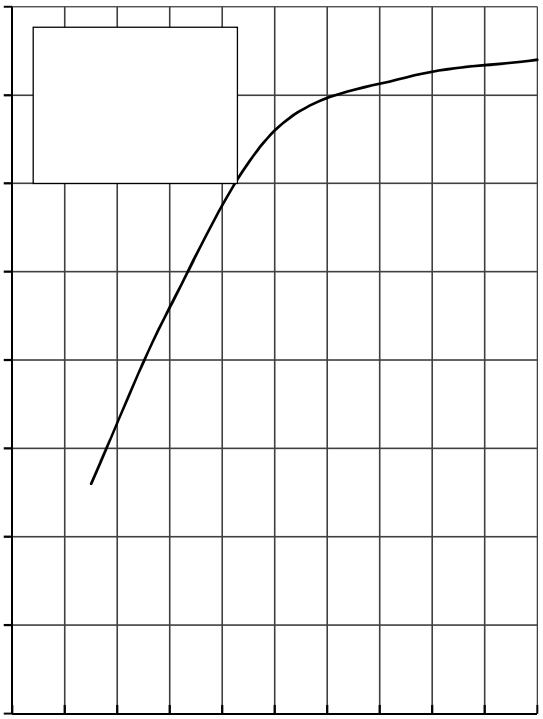
N



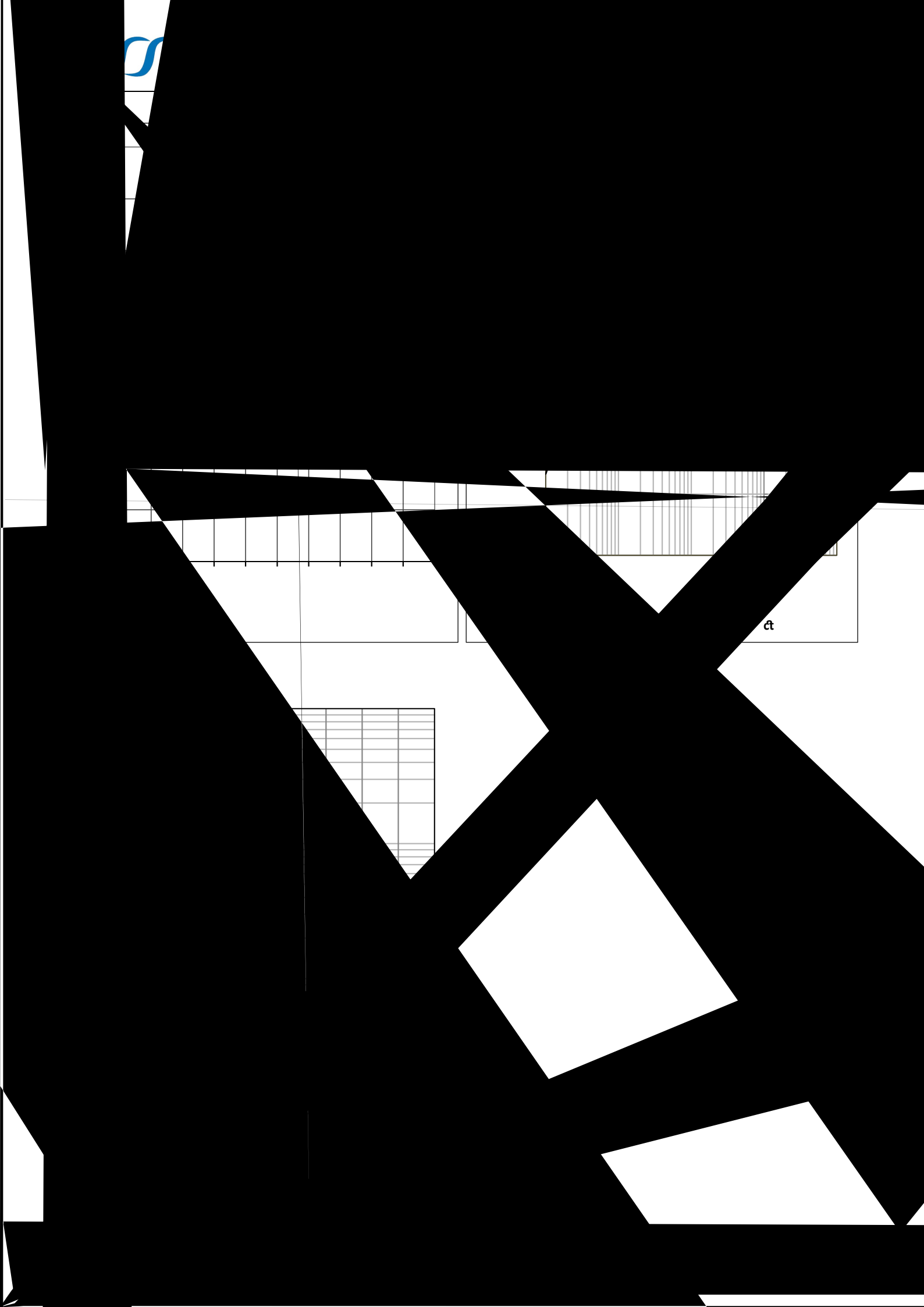
S S S

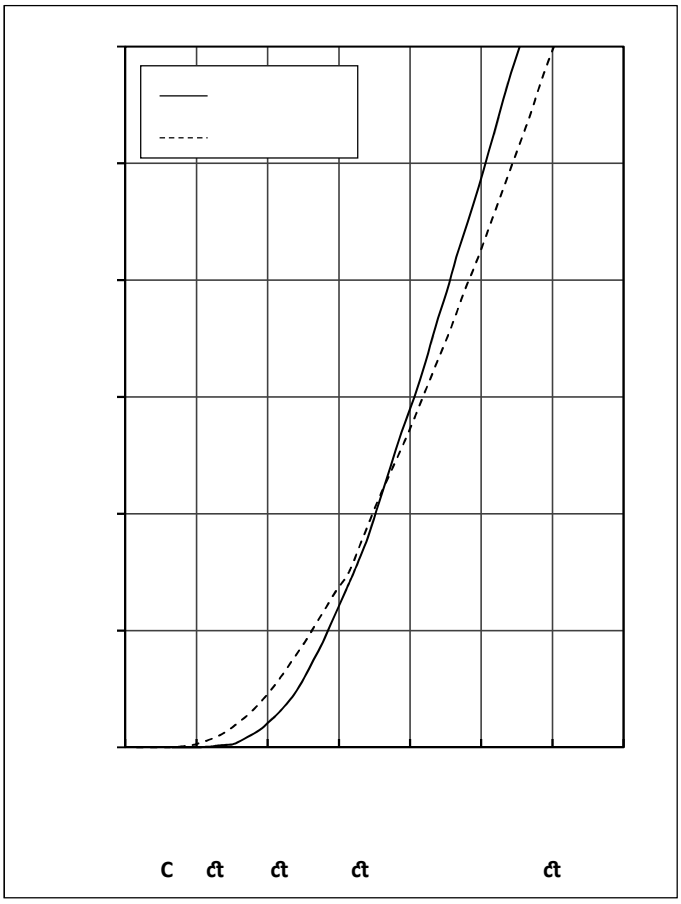


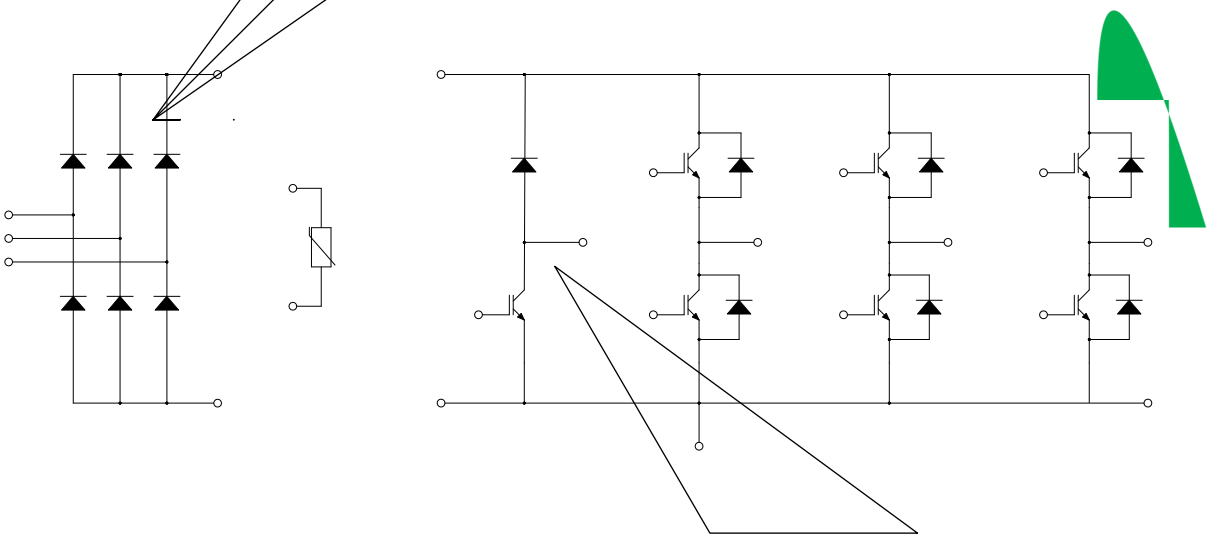
C

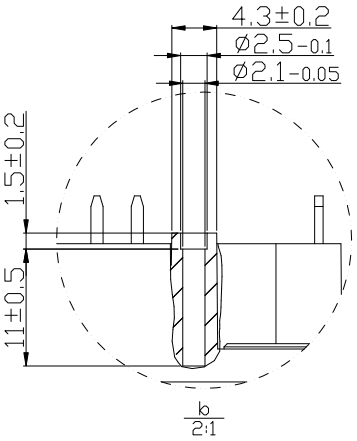


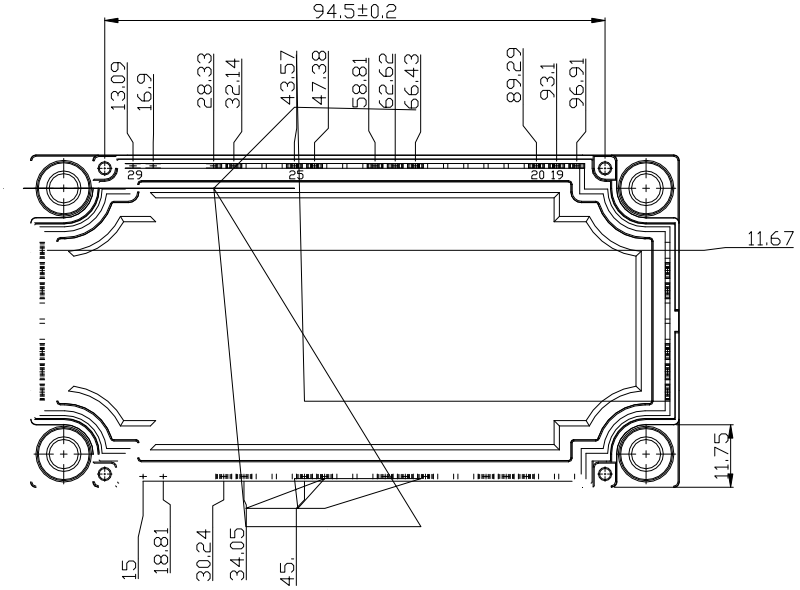
C

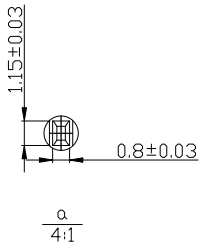







4.3±0.2
Ø2.5-0.1
Ø2.1-0.05
1.5±0.2
11±0.5
b
2:1


94.5±0.2
13.09
16.9
28.33
32.14
43.57
47.38
58.81
62.62
66.43
89.29
93.1
96.91
29
26
20
19
11.67
11.75
15
18.81
30.24
34.05
45.


1.15±0.03
0.8±0.03
a
4:1